## Answer on Question #47221

In an intrinsic semiconductor such as silicon at temperatures above absolute zero, there will be some electrons which are excited across the band gap into the conduction band and which can support current flow. When the electron in pure silicon crosses the gap, it leaves behind an electron vacancy or "hole" in the regular silicon lattice. Under the influence of an external voltage, both the electron and the hole can move across the material. In an n-type semiconductor, the dopant contributes extra electrons, dramatically increasing the conductivity. In a p-type semiconductor, the dopant produces extra vacancies or holes, which likewise increase the conductivity. It is however the behavior of the p-n junction which is the key to the enormous variety of solid-state electronic devices.

The current which will flow in an intrinsic semiconductor consists of both electron and hole current. That is, the electrons which have been freed from their lattice positions into the conduction band can move through the material. In addition, other electrons can hop between lattice positions to fill the vacancies left by the freed electrons. This additional mechanism is called hole conduction because it is as if the holes are migrating across the material in the direction opposite to the free electron movement. The current flow in an intrinsic semiconductor is influenced by the density of energy states which in turn influences the electron density in the conduction band. This current is highly temperature dependent.

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